



PTO/SB/08A (10-01)

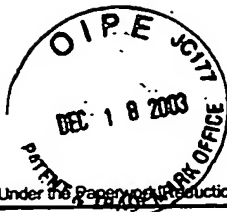
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Substitute for form 1449A/PTO				Complete if Known	
				Application Number	10/622,482
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Filing Date	July 31, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned LANDAU
				Attorney Docket Number	M4065.0724/P724
Sheet	1	of	11		

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Examiner Initials*	Cite No.†	Document Number Number-Kind Code² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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MC	AH	2002/0123169	09/05/2002	Moore et al.	
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Michael Jones 1/18/05



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				Art Unit	N/A 2815
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				First Named Inventor	Kristy A. Campbell
				Art Unit	N/A 2815
				Examiner Name	NOT YET ASSIGNED LANDAU
Sheet	3	of	11	Attorney Docket Number	M4065.0724/P724

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		†
		Country Code ²	Number ³ -Kind Code ⁴ (if known)					
	BA	56126916	JP	10/19981	Akira et al.			
	BB	WO 97/48032		12/18/1997	Kozicki et al.			
	BC	WO 99/28914		06/10/1999	Kozicki et al.			
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	BE	WO 02/21542		03/14/2002	Kozicki et al.			

Examiner Signature	<i>Michael C. Jones</i>	Date Considered	1/18/05
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*EXAMINER: Initial if reference considered/whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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Substitute for form 1449B/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/622,482		
		Filing Date	July 31, 2003		
		First Named Inventor	Kristy A. Campbell		
		Group Art Unit	N/A <i>to 2815</i>		
		Examiner Name	Not Yet Assigned <i>LANDAU</i>		
Sheet	4	of	11	Attorney Docket Number	M4065.0724/P724

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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		Filing Date	July 31, 2003
		First Named Inventor	Kristy A. Campbell
		Group Art Unit	215
		Examiner Name	Not Yet Assigned LANDAU
Sheet	5	of	11
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		Examiner Name	Not Yet Assigned LANDALL
		Attorney Docket Number	M4065.0724/P724
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		Group Art Unit	NEA 2815
		Examiner Name	Not Yet Assigned LANDAU
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Examiner Signature	<i>Matthew C. Jones</i>	Date Considered	1/18/05
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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/622,482
				Filing Date	July 21, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	2848-2815
				Examiner Name	N/A LANDAU
Sheet	1	of	3	Attorney Docket Number	M4065.0724/P724

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
mm	A	US 2004/0035401	2/2004	Ramachandran et al.	
mm	B	US 2003/0212724	11/2003	Ovshinsky et al.	
mm	C	US 2003/0048744	3/2003	Ovshinsky et al.	
mm	D	US 2003/0212725	11/2003	Ovshinsky et al.	
mm	E	US RE 37,259E	7/2001	Ovshinsky	
mm	F	US 3,271,591	9/1966	Ovshinsky	
mm	G	US 3,961,314	6/1976	Klose et al.	
mm	H	US 3,966,317	6/1976	Wacks et al.	
mm	I	US 3,983,542	11/1976	Ovshinsky	
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mm	L	US 4,267,261	5/1981	Hallman et al.	
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	N	US 4,608,296	8/1986	Keem et al.	
	O	US 4,637,895	1/1987	Ovshinsky et al.	
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	T	US 4,673,957	6/1987	Ovshinsky et al.	
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				First Named Inventor	Kristy A. Campbell
				Art Unit	2818-2815
				Examiner Name	N/A - LANDAU
Sheet	2	of	3	Attorney Docket Number	M4065.0724/P724

M	T1	US 5,414,271	5/1995	Ovshinsky et al.		
	U1	US 5,534,711	7/1996	Ovshinsky et al.		
	V1	US 5,534,712	7/1996	Ovshinsky et al.		
	W1	US 5,536,947	7/1996	Klersy et al.		
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	Y1	US 5,591,501	1/1997	Ovshinsky et al.		
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	J2	US 6,339,544	1/2002	Chiang et al.		
	K2	US 6,404,665	6/2002	Lowery et al.		
	L2	US 6,429,064	8/2002	Wicker		
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	Q2	US 6,501,111	12/2002	Lowery		
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	D3	US 6,567,293	5/2003	Lowery et al.		
	E3	US 6,569,705	5/2003	Chiang et al.		
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	H3	US 6,586,761	7/2003	Lowery		
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	J3	US 6,590,807	7/2003	Lowery		
	K3	US 6,593,176	7/2003	Dennison		
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	M3	US 6,605,527	8/2003	Dennison et al.		
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M	Q3	US 6,642,102	11/2003	Xu		

Wanda C. Fick 1/18/05

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				Examiner Name	N/A LANDAU
				Attorney Docket Number	M4065.0724/P724
Sheet	3	of	3		

R3	US 6,646,297	11/2003	Dennison		
S3	US 6,649,928	11/2003	Dennison		
T3	US 6,667,900	12/2003	Lowery et al.		
U3	US 6,671,710	12/2003	Ovshinsky et al.		
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A4	US 6,696,355	2/2004	Dennison		
B4	US 6,687,153	2/2004	Lowery		
C4	US 6,707,712	3/2004	Lowery		
D4	US 6,714,954	3/2004	Ovshinsky et al.		

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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			

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